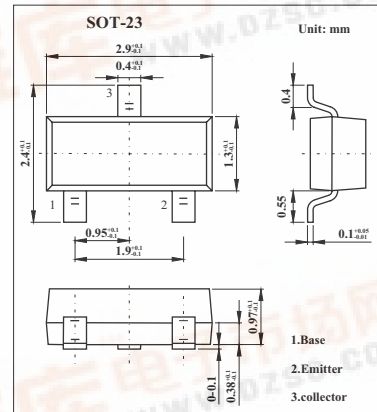


SMD Type Transistors

Silicon PNP Epitaxial
2SA1121

■ Features

- Low frequency amplifier



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector to base voltage	V _{CB0}	-35	V
Collector to emitter voltage	V _{CEO}	-35	V
Emitter to base voltage	V _{EB0}	-4	V
Collector current	I _c	-500	mA
Collector power dissipation	P _c	150	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector to base breakdown voltage	V _{(BR)CBO}	I _c = -10 mA, I _E = 0	-35			V
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _c = -1 mA, R _{BE} = ∞	-35			V
Emitter to base breakdown voltage	V _{(BR)EBO}	I _E = -10 mA, I _c = 0	-4			V
Collector cutoff current	I _{CBO}	V _{CB} = -20 V, I _E = 0			-0.5	μA
Collector to emitter saturation voltage	V _{CE(sat)}	I _c = -150 mA, I _B = -15 mA		-0.2	-0.6	V
DC current transfer ratio	h _{FE}	V _{CE} = -3 V, I _c = -10 mA	60		320	
Base to emitter voltage	V _{BE}	V _{CE} = -3 V, I _c = -10 mA		-0.64		V

■ hFE Classification

Marking	SB	SC	SD
hFE	60~120	100~200	160~320